



# PMZ200UNE

30 V, N-channel Trench MOSFET

12 March 2015

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection: 2 kV HBM
- Leadless ultra small package: 1.0 × 0.6 × 0.48 mm

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_J = 25\text{ }^\circ\text{C}$	-	-	30	V
$V_{GS}$	gate-source voltage		-8	-	8	V
$I_D$	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	1.4	A
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 1.4\text{ A}; T_J = 25\text{ }^\circ\text{C}$	-	210	250	m $\Omega$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

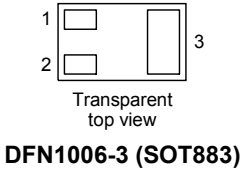
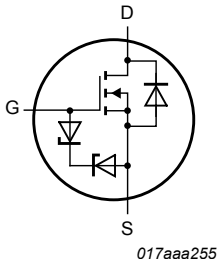


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>Transparent top view DFN1006-3 (SOT883)</p>	 <p>017aaa255</p>
2	S	source		
3	D	drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMZ200UNE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ200UNE	ZV

## 8. Limiting values

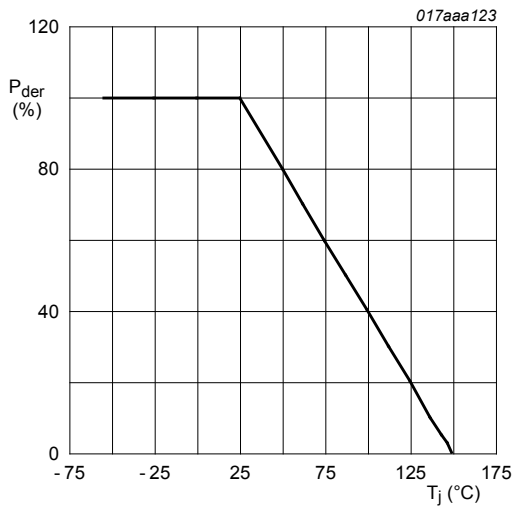
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	1.4	A
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	0.9	A
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	5	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	350	mW
			[1]	-	760	mW
		T <sub>sp</sub> = 25 °C		-	6250	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.7	A

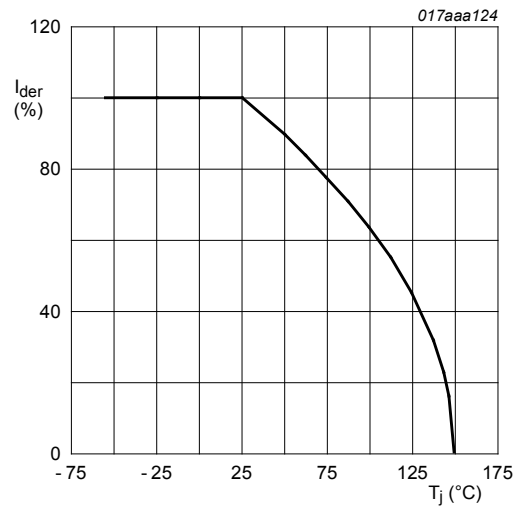
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



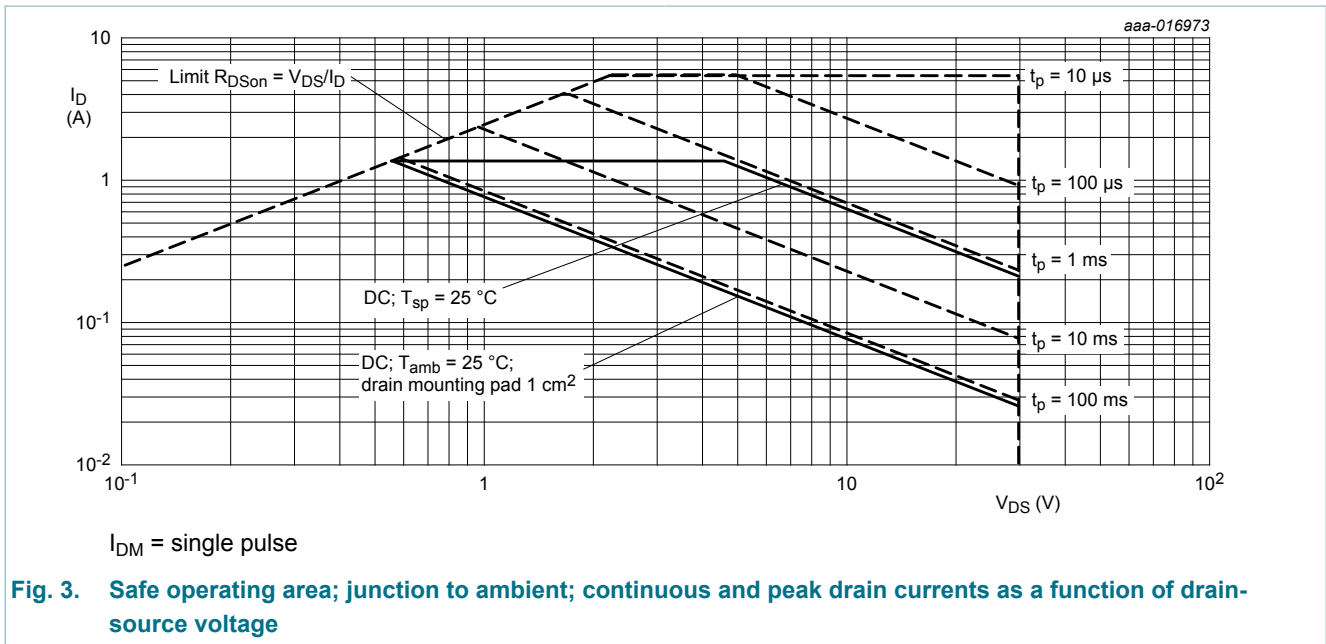
**Fig. 1. Normalized total power dissipation as a function of junction temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$



**Fig. 2. Normalized continuous drain current as a function of junction temperature**

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



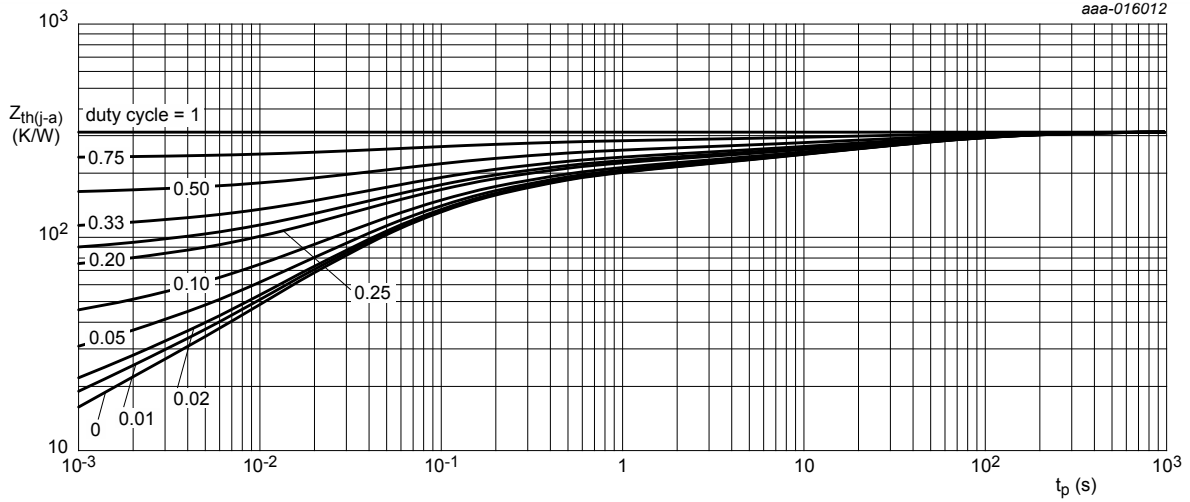
## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	315	360	K/W
			[2]	-	145	165	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	17	20	K/W

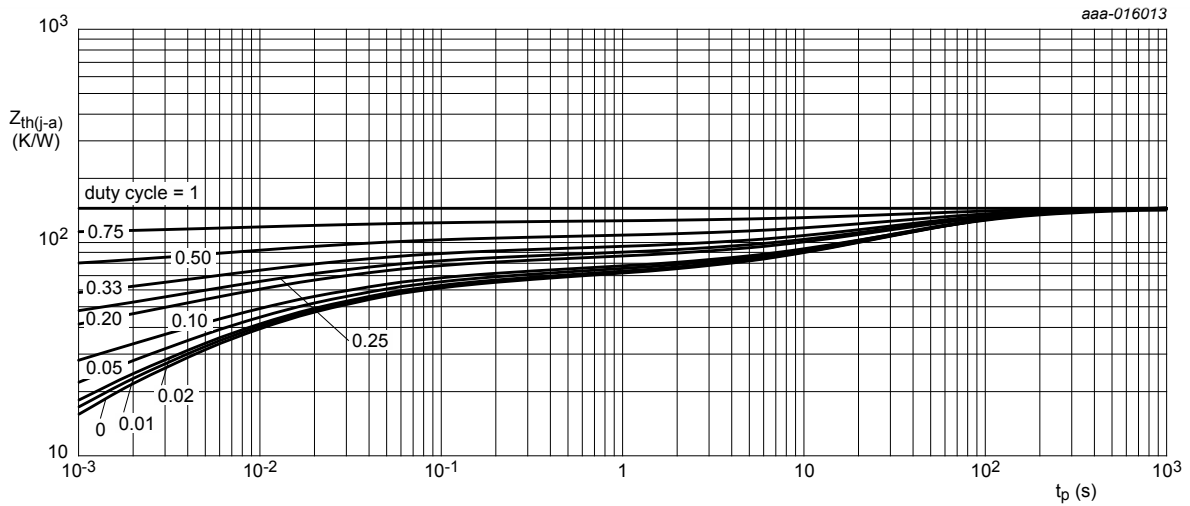
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain  $1\text{ cm}^2$ .



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ }^\circ C$	0.45	0.7	0.95	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 V$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 8 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	5	$\mu A$
		$V_{GS} = -8 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	-5	$\mu A$
		$V_{GS} = 4.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{GS} = -4.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	-1	$\mu A$
		$V_{GS} = 2.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -2.5 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	-	-100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 V$ ; $I_D = 1.4 A$ ; $T_j = 25 \text{ }^\circ C$	-	210	250	m $\Omega$
		$V_{GS} = 4.5 V$ ; $I_D = 1.4 A$ ; $T_j = 150 \text{ }^\circ C$	-	347	410	m $\Omega$
		$V_{GS} = 2.5 V$ ; $I_D = 1.2 A$ ; $T_j = 25 \text{ }^\circ C$	-	240	310	m $\Omega$
		$V_{GS} = 1.8 V$ ; $I_D = 1 A$ ; $T_j = 25 \text{ }^\circ C$	-	270	380	m $\Omega$
		$V_{GS} = 1.5 V$ ; $I_D = 0.01 A$ ; $T_j = 25 \text{ }^\circ C$	-	300	490	m $\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 10 V$ ; $I_D = 1 A$ ; $T_j = 25 \text{ }^\circ C$	-	4.1	-	S
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 15 V$ ; $I_D = 1.5 A$ ; $V_{GS} = 4.5 V$ ; $T_j = 25 \text{ }^\circ C$	-	1.6	2.7	nC
$Q_{GS}$	gate-source charge		-	0.1	-	nC
$Q_{GD}$	gate-drain charge		-	0.4	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 15 V$ ; $f = 1 \text{ MHz}$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	89	-	pF
$C_{oss}$	output capacitance		-	11	-	pF
$C_{rss}$	reverse transfer capacitance		-	9	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 V$ ; $I_D = 0.8 A$ ; $V_{GS} = 4.5 V$ ; $R_{G(ext)} = 6 \Omega$ ; $T_j = 25 \text{ }^\circ C$	-	5	-	ns
$t_r$	rise time		-	10	-	ns
$t_{d(off)}$	turn-off delay time		-	17	-	ns
$t_f$	fall time		-	3	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 0.7 A$ ; $V_{GS} = 0 V$ ; $T_j = 25 \text{ }^\circ C$	-	0.86	1.2	V

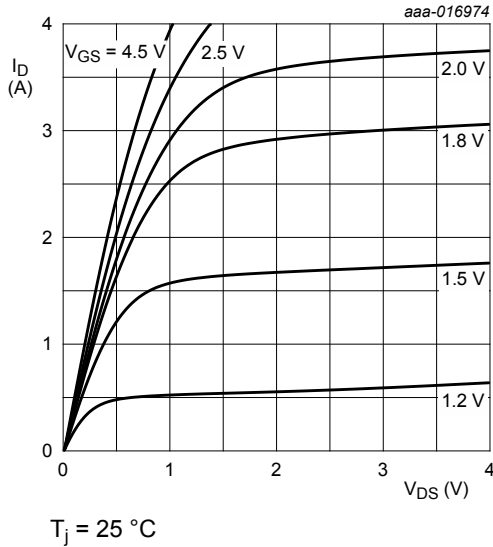


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

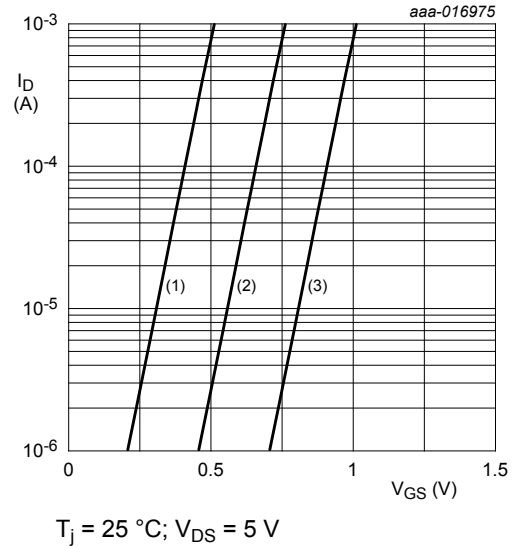


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

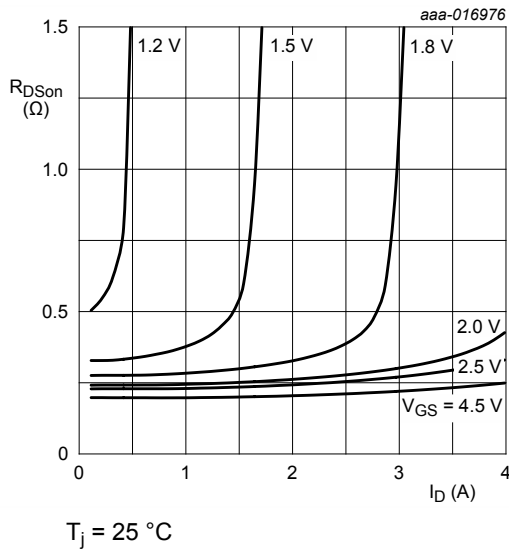


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

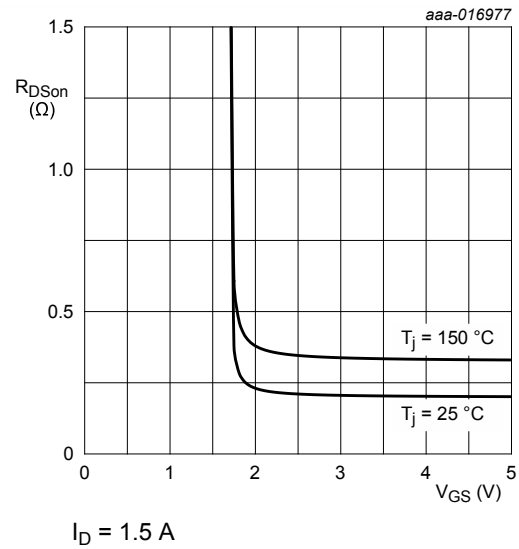
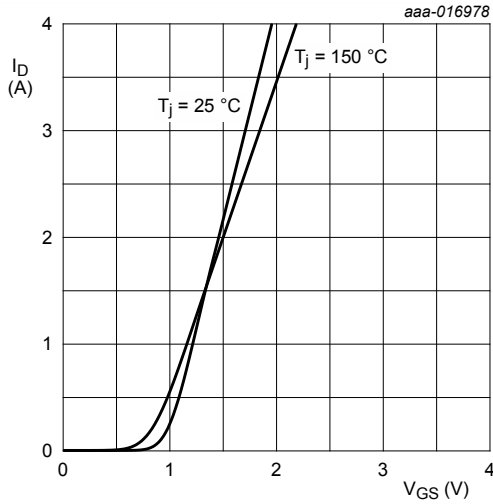
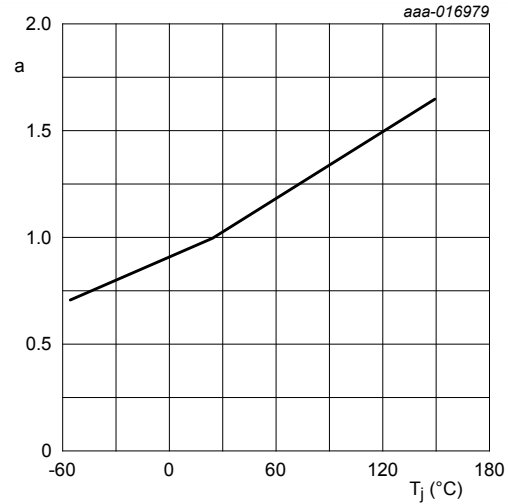


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



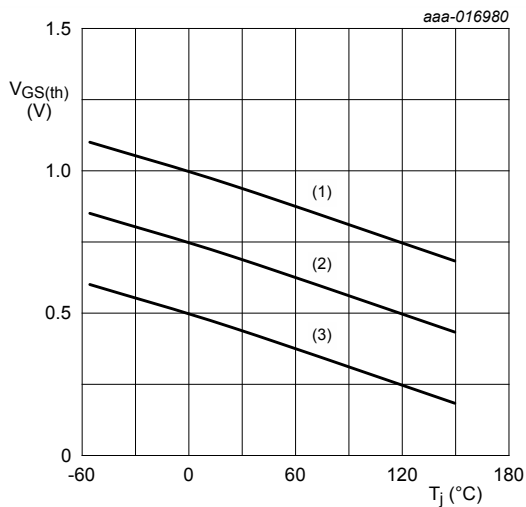
$$V_{DS} > I_D \times R_{DSon}$$

**Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



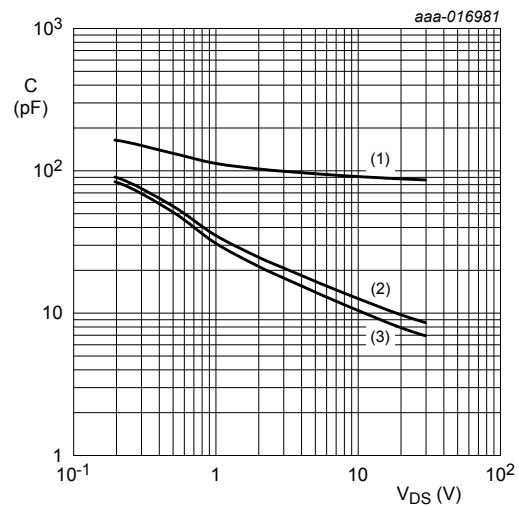
**Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$   
 (1) maximum values  
 (2) typical values  
 (3) minimum values

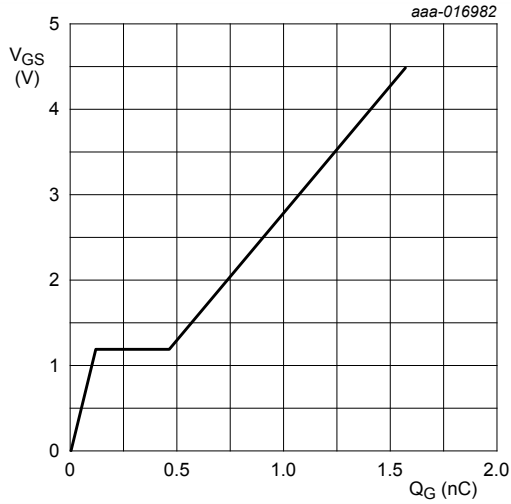
**Fig. 12. Gate-source threshold voltage as a function of junction temperature**



$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$   
 (1)  $C_{iss}$   
 (2)  $C_{oss}$   
 (3)  $C_{rss}$

**Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



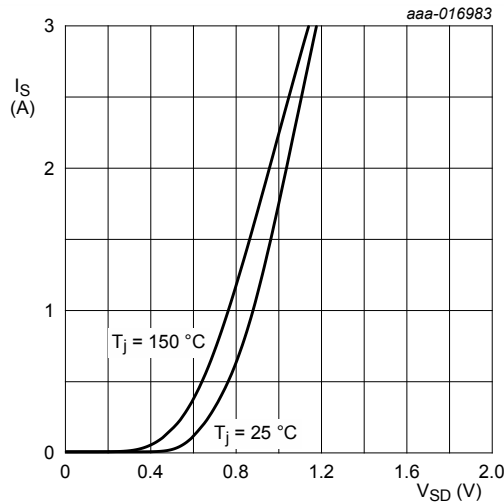


$I_D = 0.8 \text{ A}$ ;  $V_{DS} = 15 \text{ V}$ ;  $T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values



Fig. 15. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

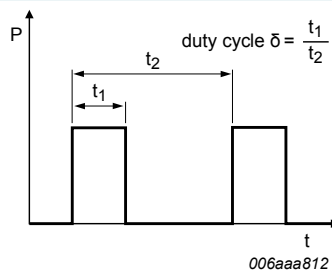


Fig. 17. Duty cycle definition

## 12. Package outline

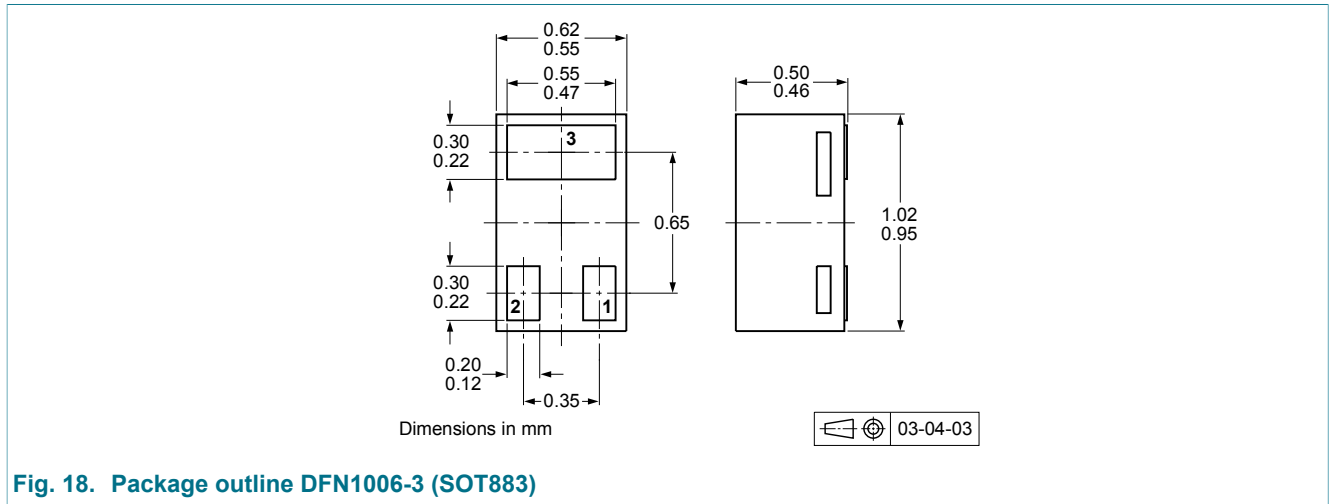


Fig. 18. Package outline DFN1006-3 (SOT883)

## 13. Soldering

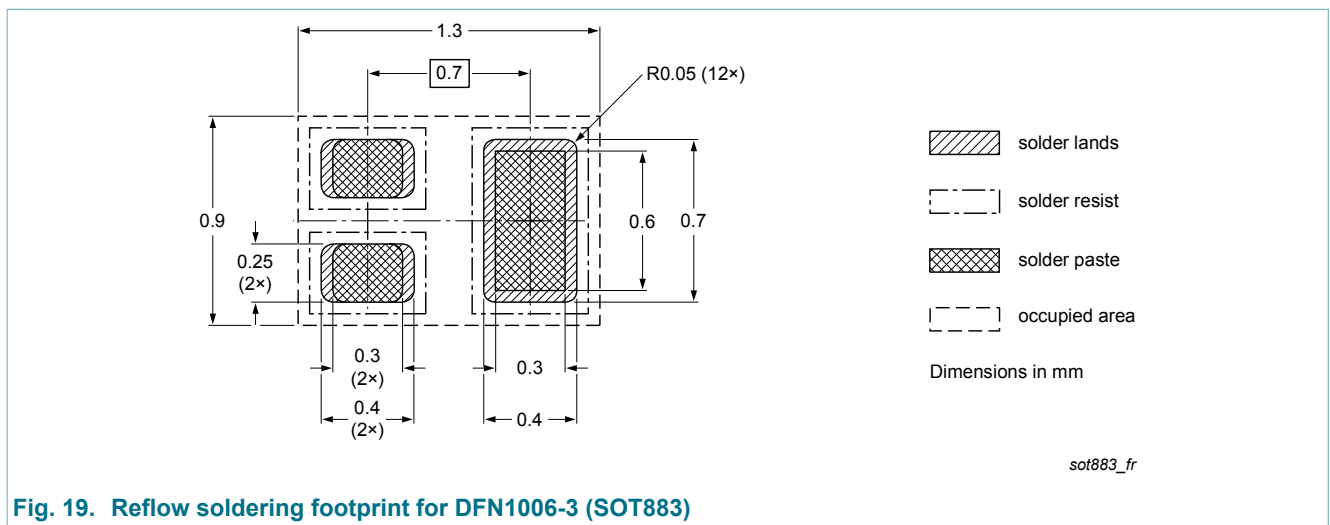


Fig. 19. Reflow soldering footprint for DFN1006-3 (SOT883)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ200UNE v.1	20150312	Product data sheet	-	-

## 15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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